



#### 60V PNP MEDIUM POWER TRANSISTOR IN SOT23

#### **Description**

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

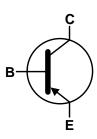
#### **Features**

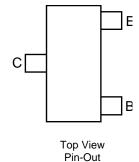
- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -1A High Continuous Collector Current
- I<sub>CM</sub> = -2A Peak Pulse Current
- $R_{SAT}$  = 295m $\Omega$  for a Low Equivalent On-Resistance
- hFE Characterized up to -2A for High Current Gain Hold Up
- Complementary NPN Type: FMMT491Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT23
- Case Material: molded plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.008 grams (Approximate)







Device Symbol

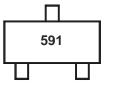
#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FMMT591QTA	Automotive	591	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



591 = Product Type Marking Code



# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I <sub>CM</sub>	-2	Α
Base Current	I <sub>B</sub>	-200	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	P <sub>D</sub>	500	mW
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 7)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

### ESD Ratings (Note 8)

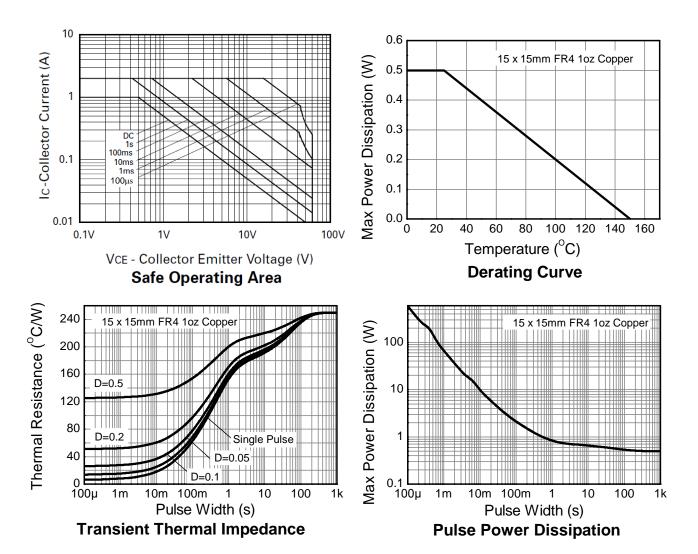
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**



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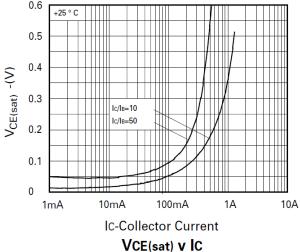
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

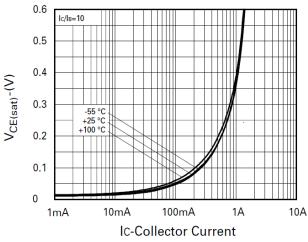
Chara	acteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage		BV <sub>CBO</sub>	-80	_	_	V	$I_{C} = -100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 9)		BV <sub>CEO</sub>	-60	_	_	V	I <sub>C</sub> = -10mA	
Emitter-Base Breakdov	vn Voltage	BV <sub>EBO</sub>	-7	-8.1	_	V	I <sub>E</sub> = -100μA	
Collector-Base Cutoff C	Current	I <sub>CBO</sub>	_	<1	-100	nA	V <sub>CB</sub> = -60V	
Emitter-Base Cutoff Cu	rrent	I <sub>EBO</sub>	_	<1	-100	nA	V <sub>EB</sub> = -5.6V	
Collector-Emitter Cut-C	Off Current	I <sub>CES</sub>	_	<1	-100	nA	V <sub>CE</sub> = -50V	
Static Forward Current Transfer Ratio (Note 9)		h <sub>FE</sub>	100 100 80 15	220 175 155 40	300 — —		$I_{C}$ = -1mA, $V_{CE}$ = -5V $I_{C}$ = -500mA, $V_{CE}$ = -5V $I_{C}$ = -1A, $V_{CE}$ = -5V $I_{C}$ = -2A, $V_{CE}$ = -5V	
Collector-Emitter Saturation Voltage (Note 9)		V <sub>CE(SAT)</sub>	l	-155 -295	-180 -350	mV	I <sub>C</sub> = - 500mA, I <sub>B</sub> = -50mA I <sub>C</sub> = - 1A, I <sub>B</sub> = -100mA	
Base-Emitter Saturation	Base-Emitter Saturation Voltage (Note 9)			965	-1200	mV	$I_C = -1A$ , $I_B = -100mA$	
Base-Emitter Turn-On	V <sub>BE(ON)</sub>	_	830	-1000	mV	$I_{C} = -1A, V_{CE} = -5V$		
Transition Frequency		f⊤	150	_	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz	
Output Capacitance		C <sub>obo</sub>	_	_	10	pF	V <sub>CB</sub> = -10V, f = 1MHz	
	Delay Time	t <sub>d</sub>	_	29.1	_			
Cwitching Time	Rise Time	t <sub>r</sub>	_	26.5	_		$V_{CC} = -10V$ , $I_{C} = -500mA$ ,	
Switching Time	Storage Time	ts	_	99.3	_	ns	$I_{B1} = -I_{B2} = -25mA$	
	Fall Time			18.9	_			

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

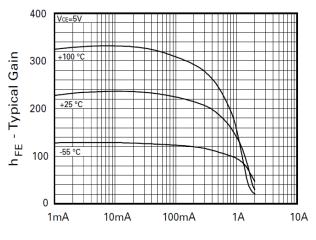


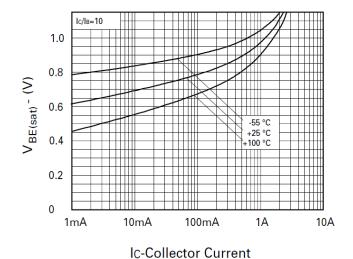
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





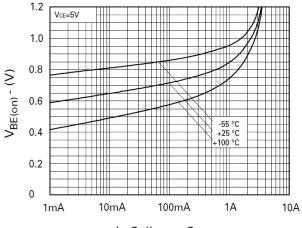
v IC VCE(sat) v Ic





Ic-Collector Current **hFE V IC** 

VBE(sat) v Ic

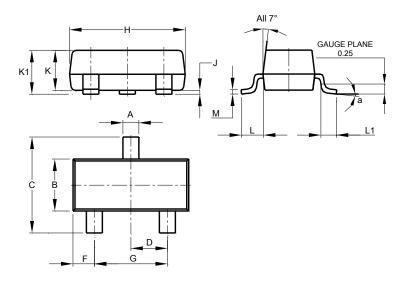




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

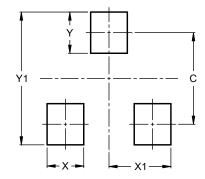


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	29			



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